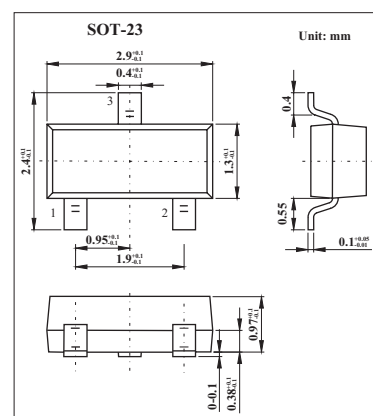


## Silicon Epitaxial Schottky Barrier Diode

## 1SS345

## ■ Features

- Small interterminal capacitance ( $C=0.45\text{pF}$  typ).
- Low forward voltage and excellent detection efficiency ( $V_F=0.35\text{V}$  max)
- High breakdown voltage ( $V_R=55\text{V}$ ).
- Very small-sized package permitting the 1SS345-applied sets to be made small and slim.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	55	V
Forward Current	$I_F$	10	mA
Power Dissipation	$P$	150	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +125	$^\circ\text{C}$
Reverse Burning	$C = 25 \text{ pF}$ $B_o$	2	erg

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F = 1 \text{ mA}$			0.35	V
Forward Current	$I_F$	$V_F = 1 \text{ V}$	10			mA
Reverse Voltage	$V_R$	$I_R = 100 \mu\text{A}$	55			V
Reverse Current	$I_R$	$V_R = 40 \text{ V}$			50	$\mu\text{A}$
Interterminal Capacitance	$C$	$V_R = 10 \text{ V}, f = 1 \text{ MHz}$		0.45		pF

## ■ Marking

Marking	AH
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